



IRFI9640GPBF Information



For Reference Only

Part Number IRFI9640GPBF **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET P-CH 200V 6.1A TO220FP**Package**TO-220-3 Full Pack, Isolated Tab

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRFI9640GPBF Specifications

Manufacturer Part Number IRF19640GPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 6.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack, Isolated Tab Series - FET Type P-Channel Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) #20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature #40W (Tc) Rds On (Max) @ Id, Vgs Domohm @ 3.7A, 10V Operating Temperature #55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer Part Number	IRFI9640GPBF
Package TO-220-3 Full Pack, Isolated Tab Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 6.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Manufacturer	Vishay Siliconix
PackageTO-220-3 Full Pack, Isolated TabSeries-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C6.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 3.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Category	Discrete Semiconductor Products
Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 6.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 6.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 44nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case To-220-3 Full Pack, Isolated Tab	Package	TO-220-3 Full Pack, Isolated Tab
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C6.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 3.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Series	-
Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C6.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 3.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C6.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 3.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs44nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)40W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 3.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Current - Continuous Drain (Id) @ 25°C	6.1A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Gate Charge (Qg) (Max) @ Vgs	44nC @ 10V
FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Input Capacitance (Ciss) (Max) @ Vds	1200pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 500 mOhm @ 3.7A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs500 mOhm @ 3.7A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3Package / CaseTO-220-3 Full Pack, Isolated Tab	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Power Dissipation (Max)	40W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Rds On (Max) @ Id, Vgs	500 mOhm @ 3.7A, 10V
Supplier Device Package TO-220-3 Package / Case TO-220-3 Full Pack, Isolated Tab	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Isolated Tab	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3
Report errors?	Package / Case	TO-220-3 Full Pack, Isolated Tab
		Report errors?

IRFI9640GPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFI9640GPBF Payment Methods





















IRFI9640GPBF Shipping Methods













If you have any question about IRFI9640GPBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com